

TRANSISTOR (PNP)

FEATURES

Complimentary to MMBT5551

MARKING:2L

SOT-23



1. BASE
2. Emitter
3. Collector

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	-160	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	-150	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	-5	V
IC	Collector Current -Continuous (集电极电流)	-0.6	A
PC	Collector Power Dissipation (耗散功率)	0.3	W
Tj	Junction Temperature (结温)	150	°C
Tstg	Storage Temperature (储存温度)	-55-150	°C

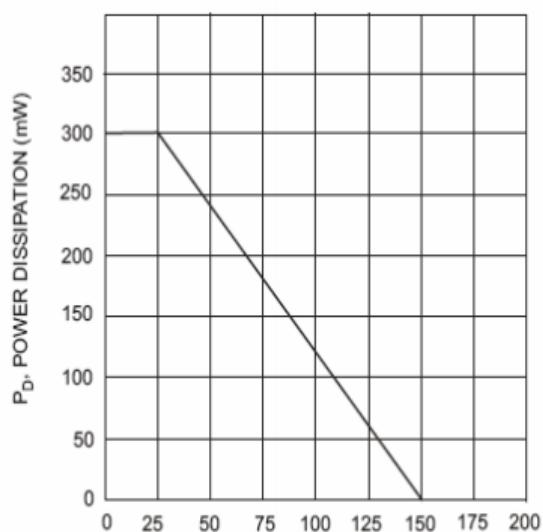
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= -100µA, IE=0	-160			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= -1mA, IB=0	-150			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=-100µA, IC=0	-5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=-120 V , IE=0			-1	µ A
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=-120V , IB=0			-10	µ A
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=-5V , IC=0			-1	µ A
DC current gain 直流电流增益	hFE	VCE=-5V, IC= -10mA	100		400	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	IC=-50mA, IB= -5mA			-0.5	V
Base-emitter saturation voltage 发射极-基极饱和压降	VBE(sat)	IC=-50mA, IB= -5mA			-1	V

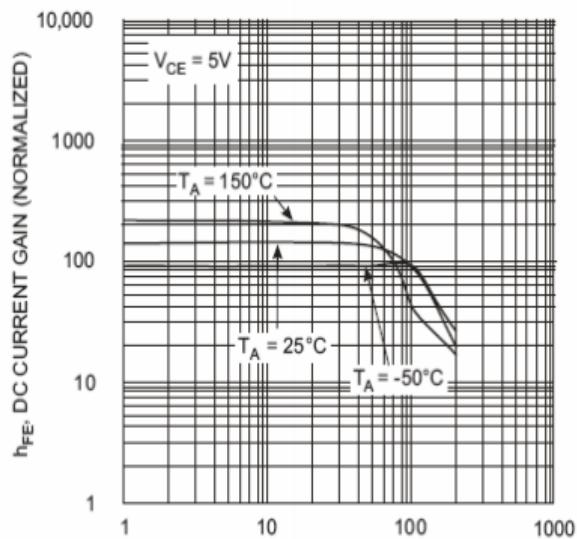
CLASSIFICATION OF hFE

Range	100-200	200-300	300-400	
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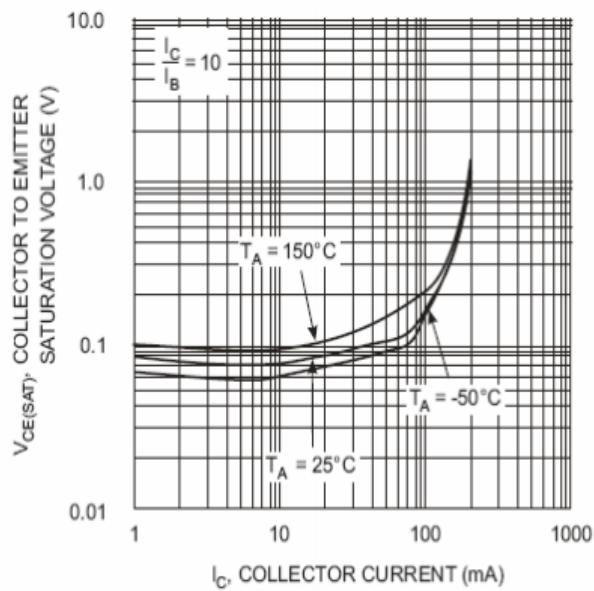
Typical Characteristics



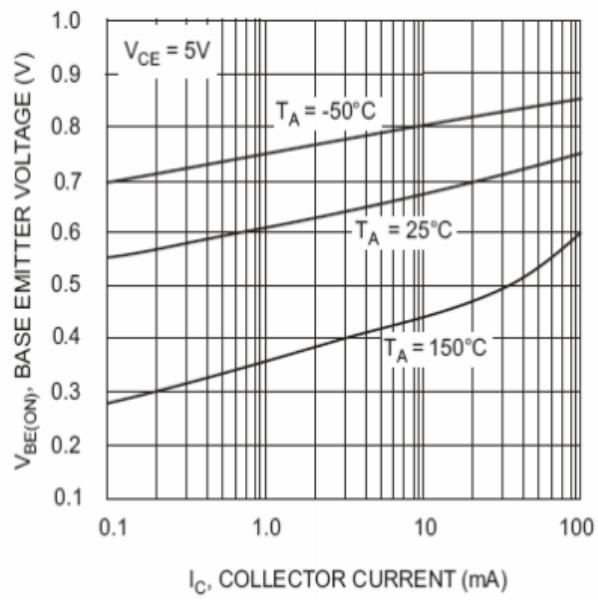
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs.
Ambient Temperature



I_C , COLLECTOR CURRENT (mA)
Fig. 3, DC Current Gain vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current